

Is Now Part of



## **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="https://www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="https://www.onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an equif prese



## FGA30N120FTD 1200 V, 30 A Field Stop Trench IGBT

## **Features**

- Field Stop Trench Technology
- High Speed Switching
- Low Saturation Voltage: V<sub>CE(sat)</sub> = 1.6 V @ I<sub>C</sub> = 30 A
- · High Input Impedance

### April 2013

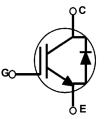
## **General Description**

Using advanced field stop trench technology, Fairchild®'s 1200V trench IGBTs offer superior conduction and switching performances for soft switching applications. The device can operate in parallel configuration with exceptional avalanche ruggedness. This device is designed for induction heating and microwave oven.

## **Applications**

· Solar Inverter, UPS, Welder, PFC





## **Absolute Maximum Ratings**

Symbol	Description		Ratings	Unit
V <sub>CES</sub>	Collector to Emitter Voltage		1200	V
V <sub>GES</sub>	Gate to Emitter Voltage		± 25	V
I <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 25°C	60	А
·C	Collector Current	@ T <sub>C</sub> = 100°C	30	А
I <sub>CM (1)</sub>	Pulsed Collector Current	@ T <sub>C</sub> = 25°C	90	A
I <sub>F</sub>	Diode Continuous Forward Current	@ T <sub>C</sub> = 100 <sup>o</sup> C	30	А
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	339	W
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	132	W
TJ	Operating Junction Temperature		-55 to +150	°C
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	5	300	°C

Notes: 1: Repetitive rating: Pulse width limited by max. junction temperature

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case	-	0.38	°C/W
$R_{\theta JC}(Diode)$	Thermal Resistance, Junction to Case	-	1.2	°C/W

$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to An		mbient		-	40		°C/W	
Packag tion	e Marking	and Ordering I	nforma- 🧭						
🥖 Dev	rice Marking	Marking Device		Eco S	Status	Packaging Type Tube		Qty per Tu 30ea	
FG	FGA30N120FTD FGA30N120FTDTU		TO-3PN	RoHS	5				
Electric	al Charact	reen" Eco Status, pleas eristics of the l	<b>GBT</b> $T_{C} = 25^{\circ}C$ unles	ss otherwise noted	1		1		
Symbol	Pa	arameter	Test Cond	itions Mir		Тур.	Max	. Unit	
Off Chara	cteristics								
BV <sub>CES</sub>		tter Breakdown Voltage	V <sub>GE</sub> = 0V, I <sub>C</sub> = 250	μA	1200	-	-	V	
I <sub>CES</sub>	Collector Cut-O	-		$V_{CE} = V_{CES}, V_{GE} = 0V$		-	1	mA	
I <sub>GES</sub>	G-E Leakage C	urrent	$V_{GE} = V_{GES}, V_{CE} =$		-	-	±250	) nA	
					1	]	1		
	G-E Threshold	Voltage	$l_0 = 30 \text{ mA}        $	/05	3.5	6	7.5	V	
V <sub>GE(th)</sub>		volidge	$I_{\rm C} = 30 \text{A}, V_{\rm CE} = 15$	$I_{C} = 30$ mA, $V_{CE} = V_{GE}$		1.6	2	V	
V <sub>CE(sat)</sub>	CE(sat) Collector to Emitter Saturation Voltage		$I_{\rm C} = 30$ A, $V_{\rm GE} = 15$ $I_{\rm C} = 30$ A, $V_{\rm GE} = 15$			-	2		
. /			$T_{\rm C} = 125^{\circ}{\rm C}$		-	2.0	-	V	
Dynamic (	Characteristics								
C <sub>ies</sub>	Input Capacitar	ice			-	5140	-	pF	
C <sub>oes</sub>	Output Capacita	ance	V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V, f = 1MHz		-	150	-	pF	
C <sub>res</sub>	Reverse Transf	er Capacitance			-	95	-	pF	
Switching	Characteristics								
t <sub>d(on)</sub>	Turn-On Delay	Time			-	31	-	ns	
t <sub>r</sub>	Rise Time		1		-	101	-	ns	
t <sub>d(off)</sub>	Turn-Off Delay	Time	V <sub>CC</sub> = 600V, I <sub>C</sub> = 3	0A,	-	198	-	ns	
t <sub>f</sub>	Fall Time		R <sub>G</sub> = 10Ω, V <sub>GE</sub> = 1	5V,	-	259	-	ns	
Eon	Turn-On Switch	ing Loss	Resistive Load, T <sub>C</sub>	Resistive Load, T <sub>C</sub> = 25 <sup>o</sup> C		0.54	-	mJ	
E <sub>off</sub>	Turn-Off Switch	ing Loss				1.16	1.51	mJ	
E <sub>ts</sub>	Total Switching	Loss			-	1.70	-	mJ	
t <sub>d(on)</sub>	Turn-On Delay	Time				40	-	ns	
t <sub>r</sub>	Rise Time				-	127	-	ns	
t <sub>d(off)</sub>	Turn-Off Delay	Time	V <sub>CC</sub> = 600V, I <sub>C</sub> = 3	0A,	-	211	-	ns	
t <sub>f</sub>	Fall Time		$R_G = 10\Omega$ , V <sub>GE</sub> = 1 Resistive Load, T <sub>C</sub>	5V, = 125°C	-	364	-	ns	
E <sub>on</sub>	Turn-On Switch	ing Loss		- 12510	-	0.74	-	mJ	
E <sub>off</sub>	Turn-Off Switch	ing Loss			-	1.63	-	mJ	
E <sub>ts</sub>	Total Switching	Loss			-	2.37	-	mJ	
Qg	Total Gate Char	ge			-	208	-	nC	
Q <sub>ge</sub>	Gate to Emitter	Charge	V <sub>CE</sub> = 600V, I <sub>C</sub> = 3 V <sub>GE</sub> = 15V	0A,	-	41	-	nC	
			V <sub>GE</sub> = 15V						

Symbol	Parameter	Test Conditions		Min.	Тур.	Мах	Unit
Ven	V <sub>FM</sub> Diode Forward Voltage	I <sub>F</sub> = 30A	T <sub>C</sub> = 25°C	-	1.3	1.7	V
* FIM			T <sub>C</sub> = 125 <sup>o</sup> C	-	1.3	-	
t <sub>rr</sub>	Diode Reverse Recovery Time	- I <sub>F</sub> =30A, di/dt = 200A/μs	T <sub>C</sub> = 25 <sup>o</sup> C	-	730	-	ns A
·rr			T <sub>C</sub> = 125°C	-	775	-	
Irr	Diode Peak Reverse Recovery Current		T <sub>C</sub> = 25 <sup>o</sup> C	-	43	-	
			T <sub>C</sub> = 125 <sup>o</sup> C	-	47	-	
Q <sub>rr</sub>	Diode Reverse Recovery Charge		T <sub>C</sub> = 25°C	-	5.9	-	μC
∽II.			$T_{\rm C} = 125^{\rm o}{\rm C}$	-	18.2	-	μΟ

### **Typical Performance Characteristics** Figure 1. Typical Output Characteristics 180 180 T<sub>C</sub> = 25<sup>o</sup>C 20V 150 17V 15V Collector Current, Ic [A] Collector Current, Ic [A] 120 12V 90 60 10V 9V 30 V<sub>GE</sub> = 8V 0 2 4 6 Collector-Emitter Voltage, V<sub>CE</sub> [V] 0 8 **Figure 3. Typical Saturation Voltage** Characteristics 120 Common Emitter V<sub>GE</sub> = 15V 100 $T_{\rm C} = 25^{\rm o} {\rm C}$ — Collector Current, I<sub>c</sub> [A] Collector Current, Ic [A] T<sub>C</sub> = 125<sup>o</sup>C .... 80 60 40 20 0 0 2 4 6 Collector-Emitter Voltage, V<sub>CE</sub> [V] Figure 5. Saturation Voltage vs. Case **Temperature at Variant Current Level** 3.0 Common Emitter V<sub>GE</sub> = 15V Collector-Emitter Voltage, V<sub>CE</sub> [V] Collector-Emitter Voltage, V<sub>CE</sub> [V] 60A 2.5 2.0 30A 1.5 $I_{\rm C} = 10A$ 1.0 125 25 50 75 100 Collector-EmitterCase Temperature, T<sub>c</sub> [°C]

### Figure 2. Typical Output Characteristics

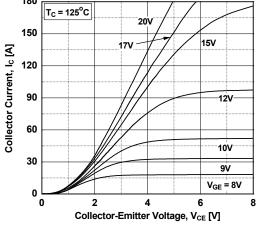
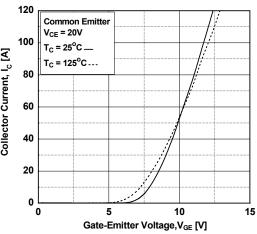
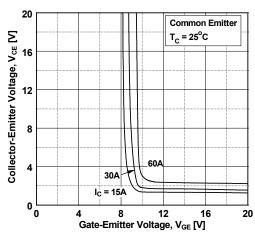


Figure 4. Transfer Characteristics







## **Typical Performance Characteristics**



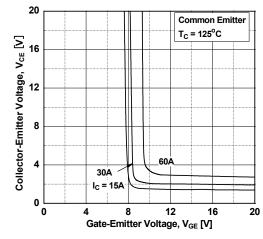
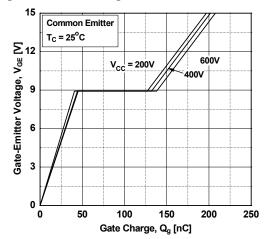


Figure 9. Gate charge Characteristics





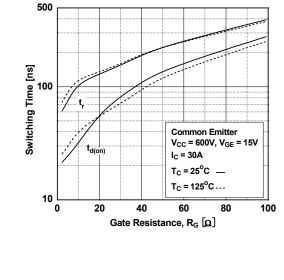


Figure 8. Capacitance Characteristics

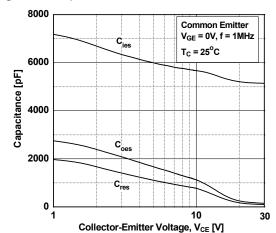


Figure 10. SOA Characteristics

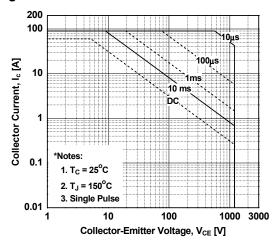
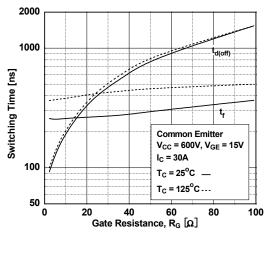
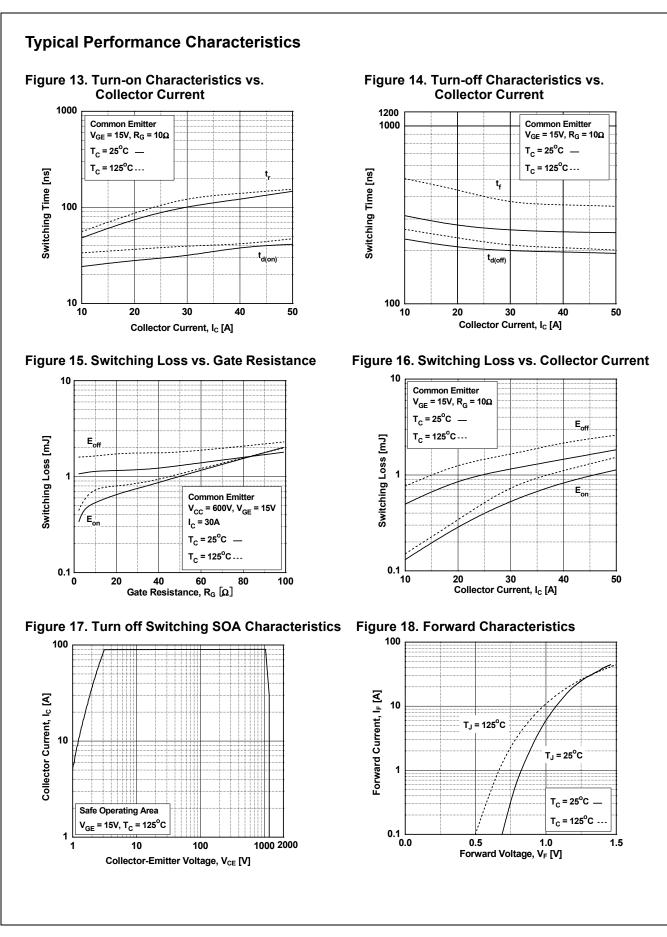


Figure 12. Turn-off Characteristics vs. Gate Resistance





# **Typical Performance Characteristics** Figure 19. Reverse Current 50 Reverse Recovery Currnet, I<sub>rr</sub> [A] 200A/µs 40

di/dt = 100A/µs

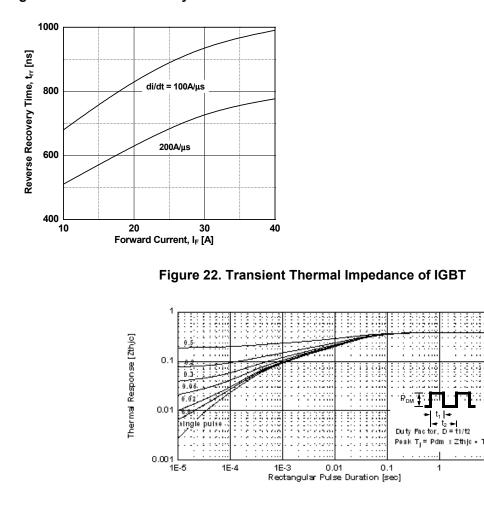
20 30 Forward Current, I<sub>F</sub> [A]



30

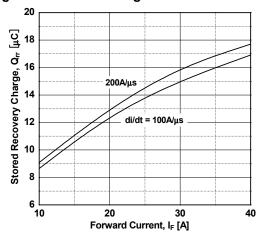
20

10

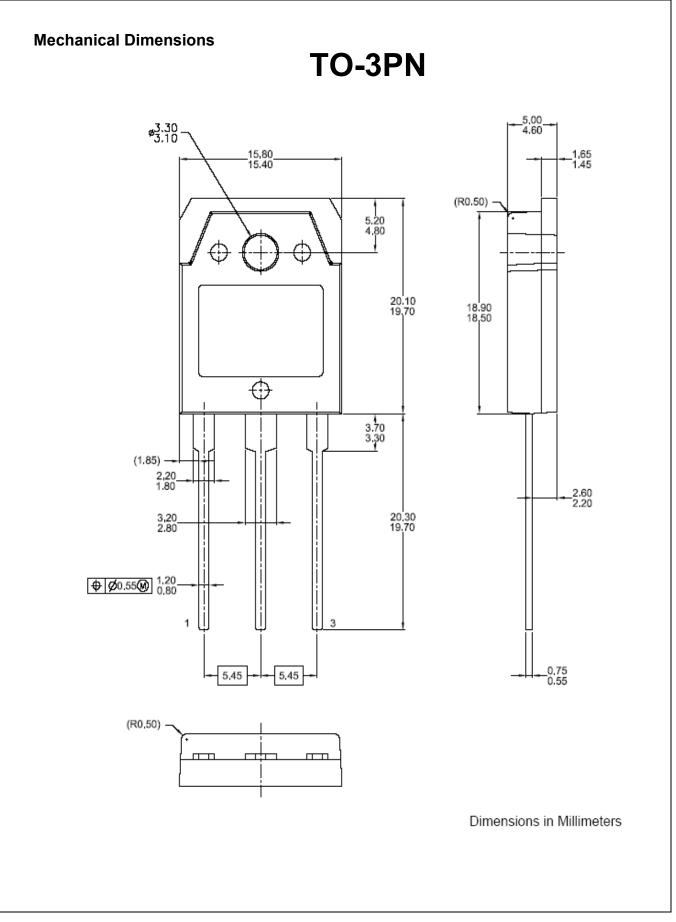


40

### Figure 20. Stored Charge



10



8

## FAIRCHIL

SEMICONDUCTOR

### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

2Cool™ FPS™ Sync-Lock™   AccuPower™ F.PFS™ PowerTrench®   BitsiC™ Global Power ResourceSM PowerXS™   Build it Now™ Green Bridge™ Programmable Active Droop™ TinyBock™   CorePOWER™ Green FPS™ QFET® TinyCoic®   CorePOWER™ Green FPS™ QS™ TinyCoic®   CorePOWER™ Green FPS™ QS™ TinyLogic®   Curtent Transfer Logic™ IntelliMAX™ Saving our world, 1mW/W/kW at a time™ TinyPower™   Dual Cool™ Marking Small Speakers Sound Louder Saving our world, 1mW/W/kW at a time™ TinPeWI™   ESBC™ MicroPak™ SmartMax™ TinyEogic® TinyBock™   ESBC™ MicroPak™ SuperSot™-3 UHC® UHC®   Fairchild® MicroPak™ SuperSot™-3 UHC® UHC®   Fairchild® MicroPak™ SuperSot™-3 UHC® UHC®   FAC
---

\*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

### DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

- Life support devices or systems are devices or systems which, (a) are 1. intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### **PRODUCT STATUS DEFINITIONS** Definition of Terms

Datasheet Identification Product Status		Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
		Rev. I6

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly ori indirectly, any claim of personal injury or death

### PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

## **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for IGBT Transistors category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below :

748152A APT20GT60BRDQ1G APT50GT60BRG NGTB10N60FG STGFW20V60DF APT30GP60BG APT45GR65B2DU30 GT50JR22(STA1ES) TIG058E8-TL-H VS-CPV364M4KPBF NGTB25N120FL2WAG NGTG40N120FL2WG RJH60F3DPQ-A0#T0 APT40GR120B2SCD10 APT15GT120BRG APT20GT60BRG NGTB75N65FL2WAG NGTG15N120FL2WG IXA30RG1200DHGLB IXA40RG1200DHGLB APT70GR65B2DU40 NTE3320 IHFW40N65R5SXKSA1 APT70GR120J APT35GP120JDQ2 IKZA40N65RH5XKSA1 IKFW75N65ES5XKSA1 IKFW50N65ES5XKSA1 IKFW50N65EH5XKSA1 IKFW40N65ES5XKSA1 IKFW60N65ES5XKSA1 IMBG120R090M1HXTMA1 IMBG120R220M1HXTMA1 XD15H120CX1 XD25H120CX0 XP15PJS120CL1B1 IGW30N60H3FKSA1 STGWA8M120DF3 IGW08T120FKSA1 IGW75N60H3FKSA1 HGTG40N60B3 FGH60N60SMD\_F085 FGH75T65UPD STGWA15H120F2 IKA10N60TXKSA1 IHW20N120R5XKSA1 RJH60D2DPP-M0#T2 IKP20N60TXKSA1 IHW20N65R5XKSA1 IDW40E65D2FKSA1